Fate of Fluorine Determination in Exhaust from NF₃-Based CVD Chamber Cleans

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Overview

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- III. AMAT Remote Clean[™] Technology
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Project Objectives

Determine effect of increased F₂ in exhaust system and effect on emissions treatment infrastructure

- Quantify F₂ in segregated acid exhaust duct (FRP) downstream of tool equipped with Remote Clean[™]
- Measure emissions using RGA, FTIR, FCS
 - Quantify F_2 emissions and F_2 to HF conversion efficiency
 - as a function of H_2O -to- F_2 ratio (damper position)
 - reaction time (damper position and sampling point)
- Evaluate FCS technology as alternative to RGA/impinger/IC
- Perform materials compatibility study of exhaust duct polymeric coupons placed in exhaust stream (F₂, HF)
- Determine if OF₂ is produced
- Calculate fluorine mass balance

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Fluorine Emission Regulatory Issues

 $^{\bullet}NF_{3}$ chamber clean F_{2} emissions are 6X $C_{2}F_{6}$

- impacts on scrubber efficiency, fluoride ion in wastewater

- F₂ is not a HAP as defined by EPA in 40 CFR 63
 - F₂ regulated by states (TNRCC) New Source Review (NSR)
 - NSR insures ground level concentrations are below ESL
- ESL (Effects Screening Level) evaluates:
 - potential health effects, odor potential, potential effects on vegetation, corrosion potential \rightarrow not ambient air standards
- ESL for F_2 is very low--2 μ g/m³ (arsine is 1.6 μ g/m³)
- F₂ is a Toxic Release Inventory (TRI) reportable chemical if used or generated above a certain level
 - current thresholds: 10,000 lb used or 25,000 lb generated

 \Rightarrow included are F_2 from NF₃ cleans and etch emissions





Fluorine Reactivity

- Highly electronegative, strongest oxidizer
- Small atomic radius
- Reactivity due to small size (0.71Å) high nuclear charge
- Thermodynamically favored reaction with water:

 $F_{2} + H_{2}O \rightarrow HOF + HF$ $HOF + H_{2}O \rightarrow H_{2}O_{2} + HF$ $HOF + H_{2}O_{2} \rightarrow HF + H_{2}O + O_{2}$ $F_{2} + H_{2}O_{2} \rightarrow 2HF + O_{2}$ Production: 2F + 2H O $\rightarrow 4HE + O_{2}$

- Net Reaction: $2F_2 + 2H_2O \rightarrow 4HF + O_2$
- In caustic media:

2F₂ + H₂O --> 2HF + OF₂

OF₂ production increases in alkaline solutions (esp. NaOH)

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AMAT Remote Clean[™] Technology

- Compact, lid-mounted, point of use
- Low-field torroidal microwave (2.45 GHz)
- No consumables
- Converts 95-99% NF₃ to atomic fluorine
- No ion bombardment
 - increased chamber kit longevity
- F₂ cleans remote chamber areas
 - increased time between wet cleans
- Faster clean times (30%--DxZ, 65%--DxL)
 - increased throughput
- Improved film deposition uniformity
- Uses up to 50% NF₃ (Ar balance)
 - 0.1 to 4.0 slm total gas flow, 1-8 Torr

DigitalDNA[™] Laboratories—April 5, 2001 —8 NSF/SRC Engineering Research Center for Environmentally Benign Semiconductor Manufacturing Remote Clean[™] Unit on DxZ Chamber



Experimental Methodology Continuous air flow measurements made using velocimeter

- Mechanical pump purge regulated by MFC
- Ambient air (45% R.H., 6800 ppm H₂O) introduced to duct

Increased H₂O in duct using humidifier

- Damper controls H₂O-to-F₂ ratio and reaction time
 - H₂O-to-F₂ ratio ranges from 4.4-to-1 to 45.8-to-1
 - Reaction time ranges from 0.15 to 5 sec
- Analytical: extractive FTIR, atmospheric pressure RGA, FCS
 - Pneumatically switched dual-cell FTIR (10 cm, 10 m)
 - All instruments have common sampling point
 - Heat-traced and purged transfer lines (except FCS)
 - RGA and FCS calibrated using "dynamic dilution"
 - Clean recipe used: 700 sccm NF₃, 1400 sccm Ar, 900 sec

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Fluorine Test Lateral Schematic





FRP Test Lateral





cap removed during tests

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Air Flow Measurements

Damper Position (% Open)	Velocity (feet/min)	CFM	Liter/min	Negative Static Pressure (in. H ₂ O)	*H ₂ O-to- fluorine ratio
0.0%	NA	NA	NA	2.600	NA
12.5%	262	23	651	2.600	4.43
25.0%	705	62	1756	2.536	11.94
37.5%	1243	109	3087	2.556	20.99
50.0%	1773	155	4390	2.498	29.85
62.5%	2383	209	5919	2.576	40.25
75.0%	2727	238	6740	2.430	45.83
100.0%	2721	238	6740	2.439	45.83

*Based on 45% r.h., 6800 ppmv H_2O in air



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Duct Material Evaluation

Coupons placed in exhaust stream H G E Α Perform F₂ exposure analysis **HF** immersion $\rightarrow \Delta$ mass

A: PTFE (Teflon)
B: FRP (Fiberglass Reinforced Plastic)
C: FRPP (Flame

Retardant Polypropylene)

D:PVC (Polyvinylchloride)

E: PP (Polypropylene)

F: ATS (Air Tight Systems brand of FRP)

G: PVDF (Polyvinylidene fluoride or Kynar)

H: Flametec (KYTEC PVDF)

I:Corzan

J: Halar

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FTIR, RGA Sampling Arrangement



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RGA NF₃ Chamber Clean Emissions



Post-pump measurement

FRP duct measurement --F₂ below detection limit

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URS Radian Fluorine Chemical Sensor





cart system/ power supply pump laptop DigitalDNA[™] Laboratories—April 5, 2001 -

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URS Radian Fluorine Chemical Sensor (FCS)

- Real-time, solid-state gas sensing device with ppb-level sensitivity and wide measurement range
- Applicability ranges from ambient air (scrubber) to dry nitrogen (tool effluent) characterizations
- Based on the chemical interaction of F₂ with organic substrate; no known cross interferents
- Fast response, small footprint, no vacuum system required
- Calibration performed at constant flow



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FCS Operation and Performance Specifications

Measurement range	0 to percentage levels (>10000			
	ppmv)			
Measurement precision	± 2%			
Minimum detection limit	10 ppbv			
Detector response time	msec			
Sample cell operating pressures	mTorr to several atm			
Footprint	cell/detector: 12"x 3"x 3"			
Weight	cell/detector: 2 lbs			
Electrical requirements	24 VDC			
	Ambient air, tool effluent (low			
Applicable sample matrices	pressure or N ₂ diluted), water			
	saturated air or nitrogen streams			
	(wet scrubber outlets)			
	None observed for mixtures			
Chemical interferences	containing SiF ₄ , HF, O ₂ , Cl ₂ , HCl,			
	PFCs and H ₂ O			



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RGA and FCS Comparison During Clean





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FCS and FTIR NF₃ Chamber Clean Emissions



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Injection

ports

Analytical Calibration of Fluorine



Mixing Plate



Exhausted Gas Cabinet "Dynamic Dilution" Manifold

Al₂O₂ Scrubber

RGA F₂ Calibration Curve



FCS F₂ Calibration Curve



URS Radian FCS PFA Calibration Duct

Gas flow

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Fluorine DRE Summary

3.0 feet Downstream			7.25 feet Downstream			22.3 feet Downstream			28.3 feet Downstream							
Domnor		Maximum	Average			Maximum	Average			Maximum				Maximum	Average	
Sotting	Average	expected F ₂	E		Average	expected F ₂	E	۸E	Average	expected F ₂	Average F ₂		Average	expected F ₂	E	^ E
(% Open)	Flow	Concentration	¹ 2	$\Delta 1_2$	Flow	Concentration	¹ 2	$\Delta 1_2$	Flow	Concentration	Measured	$\Delta 1_2$	Flow	Concentration	¹ 2	$\Delta 1_2$
(// Open)	(slm)	by Dilution	(normal)	(%)	(slm)	by Dilution	(normal)	(%)	(slm)	by Dilution	(ppmv)	(%)	(slm)	by Dilution	(normu)	(%)
		(ppmv)	(ppmv)			(ppmv)	(pprnv)			(ppmv)				(ppmv)	(ppmv)	
12.5	1096	639	58.51	-91	1098	638	16.33	-97	1058	662	13.50	-98	1125	622	8.73	-99
25	1617	433	7.79	-98	1559	449	5.51	-99	1782	393	4.57	-99	1586	441	4.22	-99
50	5275	133	2.81	-98	5116	137	2.25	-98	5254	133	2.21	-98	5267	133	1.86	-99
75	7539	93	1.66	-98	7625	92	1.61	-98	7565	93	1.56	-98	7600	92	1.45	-98

*700 sccm F_2 injected into FRP

Fluorine as a Function of Damper Position and Downstream Distance



Fluorine Mass Balance at First Test Point

3.0 Feet Downstream

Mass Balance (F _{in} /F _{out})
21.4
17.4
35.3
37.8

*90-95% of F detected as HF

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Duct Material Evaluation Results

Coupon #	Material	Other Identifier (Tradename etc.)	Initial Coupon Mass (g)	After F ₂ Exposure (g)	After 10% HF Exposure (g)
1	PTFE	Teflon	8.74	8.74	8.74
2	FRP	Fiberglass reinforced plastic	5.13	5.13	5.29
3	FRPP	Flame retardant polypropylene Endura/Empee/Polyflam	7.92	7.92	7.92
4	PVC	Polyvinylchloride	12.38	12.36	12.36
5	PP	Polypropylene	8.04	8.02	8.02
6	ATS	ATS is a manufacturer of FRP using vinyl ester and phenolic resins	4.60	4.58	4.65
7	PVDF	polyvinylidenefluoride/Kynar	22.24	22.24	22.25
8	Flametec	Kytec-PVDF	17.88	17.88	17.89
9	Corzan	Corzan 4910 or CPVC	19.31	19.31	19.32
10	Halar	Halar ECTFE	15.92	15.94	15.92

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Project Summary

- Industry trend toward NF₃-based chamber cleans
- Measuring F₂ in an ambient air exhaust system is challenging
- F₂ conversion to HF is thermodynamically favored
 - >90% F₂ converted to HF—humidity is critical factor
 - Increased reaction time did not increase F₂ to HF conversion
- F_2 DRE increased above 98% with H_2 O-to- F_2 ratio >5-to-1
- Fluorine mass balance poor
 - Reaction on stainless steel and FRP wall surfaces may account for significant F₂ degradation
- FCS is a viable analytical technique for F₂ detection
 - more studies needed
- No OF₂ detected

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Future Work

- Publish International SEMATECH report
- Continue analytical testing of FCS
 - Perform surface analysis of substrates
- Use FCS to evaluate F₂ emissions from other processes



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